

DOCKET NO. 99-039



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: : Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball,
Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No. : 09/464,297

Filed: : December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF
OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A
SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND
AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Charlotte A. Brown

Docket No. : 99-039

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:
Assistant Commissioner for Patents, Washington, D.C. 20231

on March 20, 2003
(Date of Deposit)

John P. Taylor, Reg. No. 22,369

John P. Taylor
Signature

March 20, 2003
Date of Signature

AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

Date: March 20, 2003

Sir:

In response to the Office Action mailed January 7, 2003, please amend the application as follows: